

crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer a pad electrode for wide bonding is on the center of the upper surface of said window layer, and said second conduction-type surface ohmic electrode is composed of a plurality of electrodes.

4. (Amended) The group-III nitride semiconductor light-emitting diode as claimed in claim 1 or 2, wherein said second conduction-type surface ohmic electrodes are disposed at isometric positions from the center of said pad electrode.

11. (Amended) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer a pad electrode for wire bonding is on the center of the upper surface of said window layer, and said surface ohmic electrode is composed of a plurality of electrodes.

14. (Amended) The electrode for group-III nitride semiconductor light-emitting diodes as claimed in claim 11 or 12, wherein said surface ohmic electrodes are disposed at isometric positions from the center of said pad electrode.

19. (Amended) A method for producing an electrode for group-III nitride semiconductor light-emitting diodes, comprising
forming a plurality of surface ohmic electrodes in contact with a surface of a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure,

then covering the surface of said group-III nitride crystal layer and said surface ohmic electrodes to form a window layer comprising an electrically conducting transparent oxide crystal layer conductive with said surface ohmic electrodes, and

then forming a pad electrode for wire bonding on a center of the upper surface of said window layer conductive with said window layer.

Please add new claims 21 and 22 as follows:

21. (New) A group-III nitride semiconductor light-emitting diode comprising at least a first conduction-type single crystal substrate provided with a first conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an electrically conducting transparent oxide crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface

ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer disposed in an open light-emitting region other than a projective region of the pad electrode surface of said group-III nitride crystal layer and a pad electrode for wire bonding is on the center of the upper surface of said window layer and wherein a sum of areas of said second conduction-type surface ohmic electrodes is from 5 to 30% of a total area of said open light-emitting region.

22. (New) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer in an open light-emitting region other than a projective region of a pad electrode on the surface of said group-III nitride crystal layer and comes into contact with the surface of said group-III nitride crystal layer and said pad electrode for wire bonding is on the center of the upper surface of said window layer, wherein a sum of said surface ohmic electrodes is from 5 to 30% of a total area of the open light-emitting region.